

GSDZBZX84CXX Series

Silicon Zener Diodes

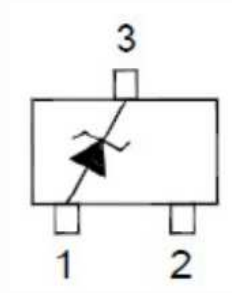
Product Description

Silicon Zener Diodes 300mW

Features

- Zener breakdown voltage range 2.4V to 51V
- Package designed for optimal automated Board assembly
- Small package size for high density applications
- Halogen-free part.

Packages & Electrical Symbol



Ordering Information



Part Number	Package	Quantity
GSDZBZX84CXXF	SOT-23	3,000 PCS

Absolute Maximum Ratings

($T_{amb}=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Conditions	Value	Unit
P_D	Power Dissipation	300	mW
V_F	Maximum Forward Voltage at $I_F=10\text{mA}$	0.9	V
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note).	417	$^{\circ}\text{C}/\text{W}$
T_{STG}	Storage Temperature Range	-65 to +150	$^{\circ}\text{C}$

(Note) : Alumina=0.4×0.3×0.024in, 99.5% alumina

Electrical Characteristics

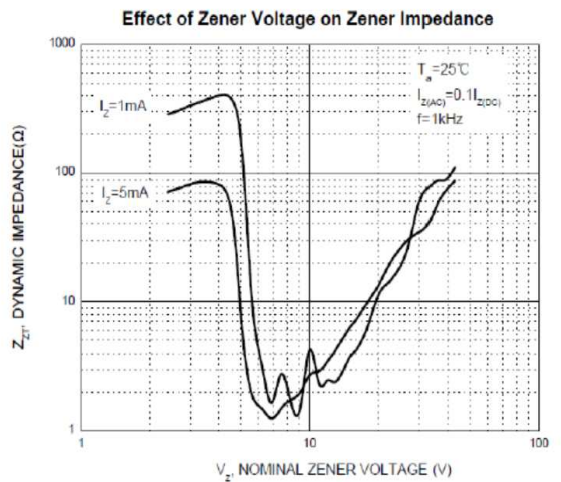
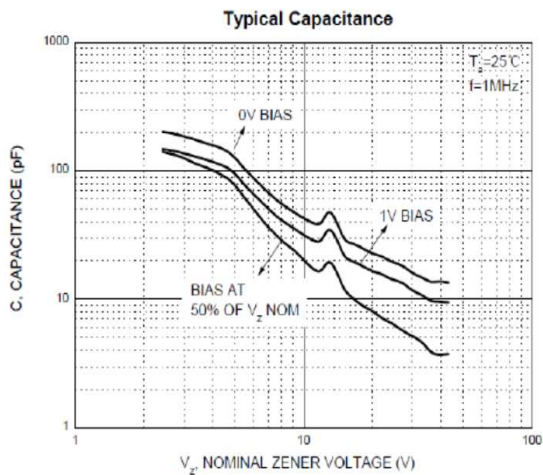
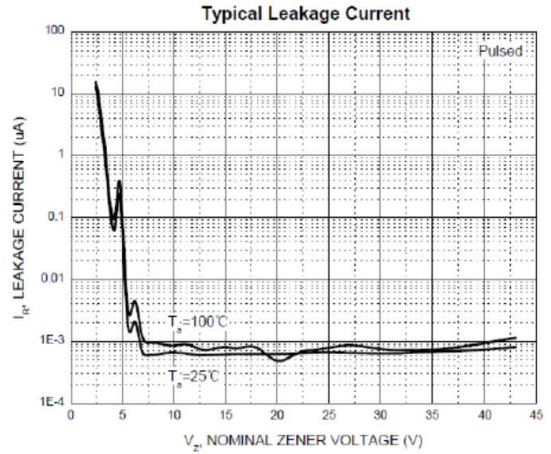
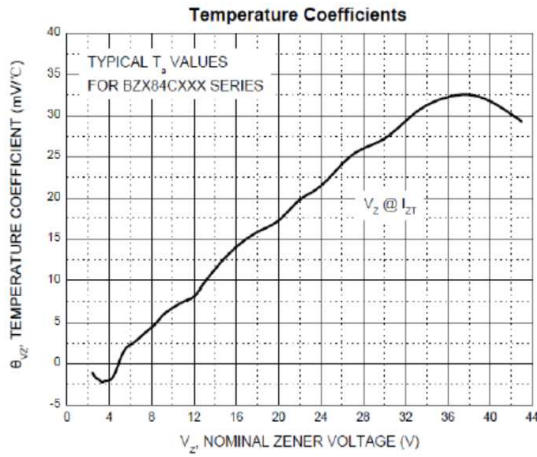
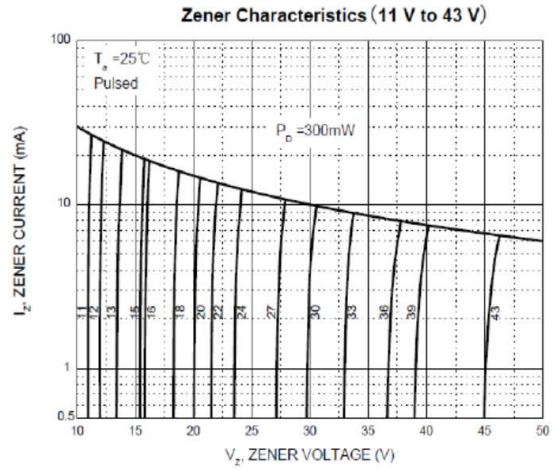
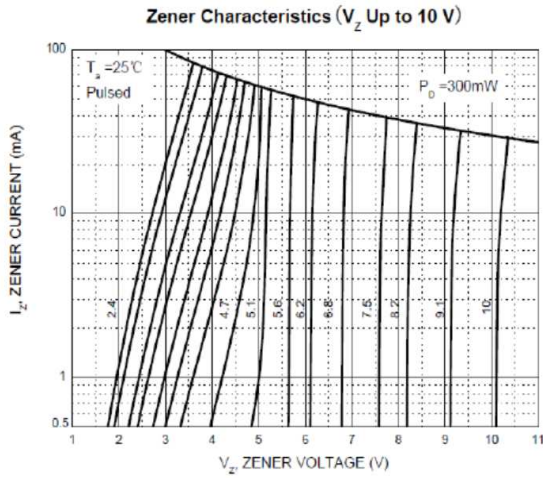
(T_{amb}=25°C Unless Otherwise Noted)

Device Type	Marking Code	V _Z (V)			Z _{ZT} @ I _{ZT} Max		Z _{ZK} @ I _{ZK} Max		I _R @ V _R Max	
		Min	Nom	Max	Ω	mA	Ω	mA	μA	V
GSDZBZX84C2V4F	C8	2.20	2.4	2.60	100	5	600	1	50	1.0
GSDZBZX84C2V7F	D8	2.50	2.7	2.90	100	5	600	1	20	1.0
GSDZBZX84C3V0F	E8	2.80	3.0	3.20	95	5	600	1	10	1.0
GSDZBZX84C3V3F	F8	3.10	3.3	3.50	95	5	600	1	5.0	1.0
GSDZBZX84C3V6F	H8	3.40	3.6	3.80	90	5	600	1	5.0	1.0
GSDZBZX84C3V9F	J8	3.70	3.9	4.10	90	5	600	1	3.0	1.0
GSDZBZX84C4V3F	K8	4.00	4.3	4.60	90	5	600	1	3.0	1.0
GSDZBZX84C4V7F	M8	4.40	4.7	5.00	80	5	500	1	3.0	2.0
GSDZBZX84C5V1F	N8	4.80	5.1	5.40	60	5	480	1	2.0	2.0
GSDZBZX84C5V6F	P8	5.20	5.6	6.00	40	5	400	1	1.0	2.0
GSDZBZX84C6V2F	R8	5.80	6.2	6.60	10	5	150	1	3.0	4.0
GSDZBZX84C6V8F	X8	6.40	6.8	7.20	15	5	80	1	2.0	4.0
GSDZBZX84C7V5F	Y8	7.00	7.5	7.90	15	5	80	1	1.0	5.0
GSDZBZX84C8V2F	Z8	7.70	8.2	8.70	15	5	80	1	0.7	5.0
GSDZBZX84C9V1F	A9	8.50	9.1	9.60	15	5	100	1	0.5	6.0
GSDZBZX84C10F	B9	9.40	10	10.60	20	5	150	1	0.2	7.0
GSDZBZX84C11F	C9	10.40	11	11.60	20	5	150	1	0.1	8.0
GSDZBZX84C12F	D9	11.40	12	12.70	25	5	150	1	0.1	8.0
GSDZBZX84C13F	E9	12.40	13	14.10	30	5	170	1	0.1	8.0
GSDZBZX84C15F	F9	13.80	15	15.60	30	5	200	1	0.05	10.5
GSDZBZX84C16F	H9	15.30	16	17.10	40	5	200	1	0.05	11.2
GSDZBZX84C18F	J9	16.80	18	19.10	45	5	225	1	0.05	12.6
GSDZBZX84C20F	K9	18.80	20	21.20	55	5	225	1	0.05	14.0
GSDZBZX84C22F	M9	20.80	22	23.30	55	5	250	1	0.05	15.4
GSDZBZX84C24F	N9	22.80	24	25.60	70	5	250	1	0.05	16.8
GSDZBZX84C27F	P9	25.10	27	28.90	80	2	300	0.5	0.05	18.9
GSDZBZX84C30F	R9	28.00	30	32.00	80	2	300	0.5	0.05	21.0
GSDZBZX84C33F	X9	31.00	33	35.00	80	2	325	0.5	0.05	23.0
GSDZBZX84C36F	Y9	34.00	36	38.00	90	2	350	0.5	0.05	25.2
GSDZBZX84C39F	Z9	37.00	39	41.00	130	2	350	0.5	0.05	27.3
GSDZBZX84C43F	A0	40.00	43	46.00	150	2	375	0.5	0.05	30.1
GSDZBZX84C47F	B0	44.00	47	50.00	170	2	375	0.5	0.05	32.9
GSDZBZX84C51F	C0	48.00	51	54.00	180	2	400	0.5	0.05	35.7

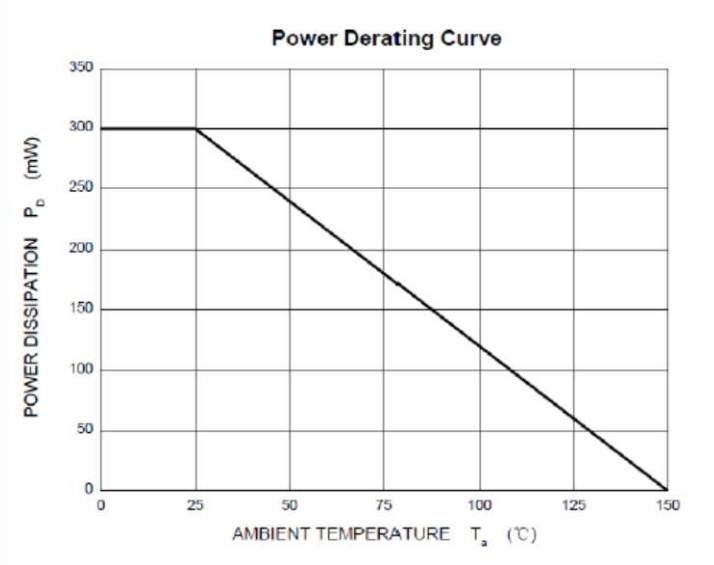
Note:

Tested with pulse tp= 20ms

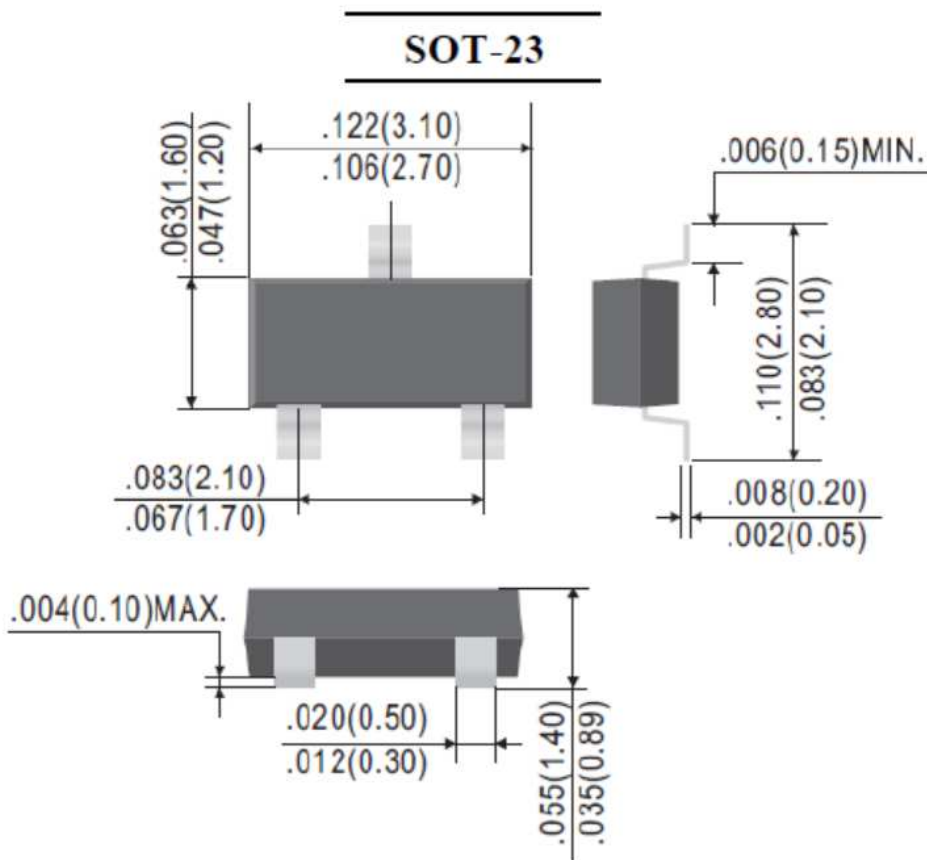
Typical Characteristics



Typical Characteristics(Continue)



Package Dimension









Dimensions in inches and (millimeters)

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